Electronic structure of tetragonal $BaK_{2-x}Ba_xBi_2O_7$ and related layer-type bismuthates

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The electronic structure of body-centered-tetragonal BaK₂Bi₂O₇, an ordered prototype of the recently synthesized perovskite-type layer compound BaK_{1.3}Ba_{0.7}Bi₂O₇, has been calculated with the use of the linear augmented-plane-wave method. In rigid-band terms, the results predict metallic properties for the entire BaK_{2-x}Ba_xBi₂O₇ alloy series, with $E_F(x)$ rising with increasing x to gradually fill a pair of nearly two-dimensional $(sp\sigma)^*$ conduction bands. For compositions x > 0.8, the onset for filling the upper $(sp\sigma)^*$ subband produces a sharp increase in the density of states. The resulting value (per Bi) is about 50% greater than that for cubic Ba_{1-y}K_yBiO₃ near the composition $(x \sim 0.8)$ should provide more favorable conditions for possible superconductivity in these BaK_{2-x}Ba_xBi₂O₇ alloys than those predicted for the nonsuperconducting $x \sim 0.7$ phase that has been prepared thus far.

Since the discovery¹ of high-temperature superconductivity in the cubic Ba_{1-x}K_xBiO₃ alloy system, with measured T_c 's that have reached the 30 K range,² efforts to synthesize new bismuthate and plumbate superconducting phases have been largely unsuccessful.³⁻⁹ The sole exception has been the observation of superconductivity $(T_c \approx 3.5 \text{ K})$ in the cubic BaPb_{1-x}Sb_xO₃ alloy system⁴ with $x \approx 0.25$. This transition temperature is significantly lower than the value $(T_c \approx 12 \text{ K})$ that was observed initially by Sleight, Gillson, and Bierstedt¹⁰ in the nearlycubic BaPb_{1-x}Bi_xO₃ system in the same composition range, $x \approx 0.25-0.30$. This suggests that the increased Bi(6s) binding energy relative to the Pb(6s) and Sb(5s) values may play an important role in enhancing the superconducting properties of the Bi-based compounds.

In their work on the Ba-Pb-O and Ba-Pb-Bi-O systems, Fu et al.⁵ discovered that these materials form a Ruddlesden-Popper-type¹¹ homologous alloy series with general composition $Ba_{n+1}(Pb_{1-x}Bi_x)_nO_{3n+1}$. These tetragonal phases consist of n perovskite-type $BaPb_{1-x}Bi_xO_3$ layers, which are separated along the c axis by rocksalt-type BaO bilayers. The n = 1 and $n = \infty$ end members of this series correspond to body-centeredtetragonal (bct) $Ba_2Pb_{1-x}Bi_xO_4$ and (nearly) cubic $BaPb_{1-x}Bi_xO_3$, respectively. The former compound shares the same K_2NiF_4 -type structure with the high- T_c cuprate superconductor $La_{2-x}Ba_xCuO_4$ (Ref. 12). Thus, these Ruddlesden-Popper phases provide an interesting structural link between the cubic bismuthate high- T_c superconductors and their tetragonal cuprate counterparts. They also provide a valuable system for investigating the influence of dimensionality on the superconducting properties of chemically similar two- and three-dimensional perovskite-type phases.

Initial efforts to induce metallic behavior and superconductivity in these Pb-based tetragonal Ruddlesden-Popper phases via $Bi \rightarrow Pb$ substitutional doping have been unsuccessful.^{6,7,9} One problem with this approach is that it ignores the successful strategy¹ of leaving the conducting Pb-O or Bi-O octahedral complexes intact and instead doping substitutionally at the chemically and electronically inactive Ba sites. However, Cava *et al.*¹³ have recently synthesized a very promising material in this regard, a K-doped, Bi-based n=2 member of the Ruddlesden-Popper series with general formula $BaK_{2-x}Ba_xBi_2O_7$ and composition $x \approx 0.7$. While superconductivity has not been observed in these samples, a simple rigid-band extrapolation of previous bandstructure results for the isostructural $Ba_{n+1}Pb_nO_{3n+1}$ series¹⁴ suggests that a slightly increased Ba composition $(x \ge 0.8)$ should produce more favorable conditions for possible superconductivity in these materials.

In order to address these issues, a scalar-relativistic version¹⁵ of the linear augmented-plane-wave (LAPW) method has been applied to calculate the electronic band properties of BaK₂Bi₂O₇ and related layered bismuthates (including Ba₂BiO₄ and Ba₃Bi₂O₇). The BaK₂Bi₂O₇ and Ba₃Bi₂O₇ results represent the ordered end-member prototypes of the BaK_{2-x}Ba_xBi₂O₇ alloy series that has been synthesized¹³ thus far only with the composition $x \approx 0.7$. These end-member band-structure results confirm the validity of a rigid-band treatment for intermediate doping compositions x. They also confirm that doping at the electronically and chemically inactive Ba site in the cubic Ba_{1-x}K_xBiO₃ alloys^{1,16,17} should also be effective here.

The present LAPW calculations have been carried out self-consistently in the local-density approximation with the use of the Wigner interpolation formula¹⁸ to treat exchange and correlation effects. The implementation¹⁵ imposes no shape approximations on either the crystalline charge density or potential. In this investigation, the LAPW basis has included plane waves with a 10.5-Ry cutoff (~770 LAPW's) and spherical-harmonic terms through l = 8 within the muffin-tin spheres. The potential and charge density have been expanded using ~9200 plane waves in the interstitial region and lattice-harmonic expansions ($l_{max} = 6$) inside the muffin-tin spheres. Brillouin-zone integrations have been carried out using a

ten-k-point sample in the $\frac{1}{16}$ irreducible Brillouin-zone wedge. The atomic Ba($5p^{6}6s^{2}$), K($3p^{6}4s$), Bi($6s^{2}6p^{3}$), and O($2s^{2}2p^{4}$) states are treated as valence electrons, while a frozen-core approximation is applied to the more tightly bound core levels.

The essential features of the $BaK_{2-x}Ba_xBi_2O_7$ structure are illustrated in Fig. 1. The primitive cell contains two perovskite-type layers with equivalent Bi sites that are octahedrally coordinated by oxygens. The $BaK_{1,3}Ba_{0,7}Bi_2O_7$ structural parameters, which have been determined by single-crystal x-ray-diffraction measurements,¹³ are summarized in Table I. According to these structural parameters, the Bi-O coordination geometry is quite symmetrical. In particular, the Bi-O bond distances $(\sim 2.14 \text{ Å})$ with the planar [O(2)] oxygens are slightly larger than the average apical-oxygen [~ 2.17 Å for O(1) and ~ 2.04 Å for O(3)] values. A similar anisotropy occurs in Ba₂PbO₄, where the Pb coordination geometry involves two short (~2.06 Å) apical Pb-O bond distances and four longer (~ 2.14 -Å) planar values.¹⁴

An interesting aspect of these x-ray structural data is the fact that they reveal a preference between the two Ba sites (types 2b and 4e, respectively) in regard to $K \rightarrow Ba$ substitution. In particular, the data analysis shows that the type-2b sites are occupied entirely by Ba atoms and the K-Ba alloying effects are confined solely to the type 4e sites. These form the rocksalt-type bilayers that separate neighboring cells along the *c* direction.

The present LAPW band-structure results for the ordered BaK₂Bi₂O₇ alloy in which these 4e sites are fully occupied by K atoms are shown in Fig. 2. The 23-band valence- and conduction-band manifold, which extends from $\sim +4$ to -11 eV, evolves from the O(2p) and Bi(6s) states. The Fermi level occurs within the lower portion of a pair of $(sp\sigma)^*$ antibonding subbands that originate from the strong Bi-O nearest-neighbor interactions. Their bonding counterparts intersect the corelike bands at lower energies (~ -10.0 and -10.5 eV), which represent the Ba(5p) and K(3p) levels, respectively. Since the lowest Ba and K conduction bands are located well above (~ 5 eV) the BaK₂Bi₂O₇ Fermi level, these constit-



FIG. 1. Primitive body-centered-tetragonal unit cell for $BaK_{2-x}Ba_xBi_2O_7$. Oxygens in the Ba, Bi, and K-Ba planes are denoted O(1), O(2), and O(3), respectively.

TABLE I. Measured (Ref. 13) atom-position parameters for the body-centered-tetragonal compound BaK_{1.3}Ba_{0.7}Bi₂O₇ with space group I4/mmm (D_{4h}^{17}) and lattice-parameter values a = 4.2477 Å and c = 21.885 Å.

Atom	Туре	x	у	Z
Ba	2b	$\frac{1}{2}$	$\frac{1}{2}$	0
$K_{1.3}Ba_{0.7}$	4e	$\frac{\frac{2}{1}}{2}$	$\frac{1}{2}$	0.189 23
Bi	4e	Ô	Ô	0.099 34
O (1)	2a	0	0	0
O(2)	8g	$\frac{1}{2}$	0	0.0914
O(3)	4e	Õ	0	0.192 3

uents essentially donate their three outer $(6s^2 \text{ and } 4s)$ electrons to the Bi(6s)-O(2p) band manifold.

The $(sp\sigma)^*$ conduction bands are very similar to those obtained previously [see Fig. 5(a) of Ref. 14] from a tight-binding treatment for the isostructural and isoelectronic compound Ba₃Pb₂O₇, where tight-binding parameters have been derived from a fit to LAPW results for Ba₂PbO₄. According to this tight-binding analysis,¹⁴ the splitting between the two $(sp\sigma)^*$ conduction bands in Fig. 2 originates from the fact that the upper $(sp\sigma)^*$ band, which is odd under reflection in the basal plane, interacts with two apical oxygens whereas the lower (even) $(sp\sigma)^*$ band interacts only with one. As expected, the main



FIG. 2. LAPW band results for $BaK_2Bi_2O_7$ along symmetry lines in the bct Brillouin zone. Those bands labeled by squares [triangles] have at least 40% Bi(6s)-O((2)p(x,y)) [Bi(6s)-O((1,3)p(z))] orbital weight within the corresponding muffintin spheres. The x's identify bands with significant (> 30%) Ba or K d-type character.

difference in the present BaK₂Bi₂O₇ bands is due to the increased binding energy (~2.4 eV) of the atomic Bi(6s) level relative to that of the corresponding Pb(6s) state. In contrast to the calculated semiconducting behavior in Ba₃Pb₂O₇, this shifts the BaK₂Bi₂O₇ ($sp\sigma$)* bands to lower energies to the extent that they overlap the nonbonding O(2p) bands and produce metallic behavior. A less obvious consequence of the increased Bi(6s) binding energy is to increase the O(2p) component of the conduction-electron states near E_F . Qualitatively, this could increase T_c by enhancing the coupling between the Fermi-surface electrons and bond-stretching oxygen phonons.

As shown by the square and triangle symbols, the orbital character of the $(sp\sigma)^*$ subbands varies systematically with wave vector and energy. The lower-energy portions of each subband involve primarily Bi(6s) $(sp\sigma)$ interactions with apical oxygen [O(1) and O(3), respectively] p(z)-type orbitals, while the uppermost states exhibit planar Bi(6s)-O(2) p(x,y) character. As discussed previously,¹⁴ this variation from apical-to-planar Bi-O bonding effects in the BaK₂Bi₂O₇ $(sp\sigma)^*$ conduction bands is a manifestation of their hybrid nature.

The band-structure results in Fig. 2 exhibit nearly two-dimensional (2D) characteristics, despite the basic isotropic character of the central Bi(6s) states. These 2D features result from the rocksalt-type K_2O_2 double-layers, which act as insulating barriers to separate neighboring BaBi₂O₅ units along the *c* axis. One obvious measure of 2D behavior is the limited dispersion exhibited by the bands along the ΓZ direction. Another is the symmetry of the bands about X and the midpoint of the ΔU line. These lines, which are coplanar in an extended-zone scheme, are separated vertically by the same ΓZ dimension $(2\pi/c)$ in the primitive Brillouin zone.

These 2D band characteristics originate from the fact that the continuity of the O(3)-Bi-O(1)-Bi-O(3) *c*-axis bonds in Fig. 1 is interrupted by the body-centering translation, which places the electronically inactive K^+ ions above and below the O(3) sites in neighboring cells. As a result, the strong apical-oxygen $(sp\sigma)$ interactions with the intermediate Bi atoms produce pairs of bonding and antibonding molecular-orbital-type states that are shifted by large energies but in turn exhibit minimal *c*axis dispersion.¹⁴

This qualitative picture is reflected by the valenceelectron charge-density results that are shown in Fig. 3. The strong nearest-neighbor Bi-O $(sp\sigma)$ bonds are identified by the long-dashed curves that represent the 0.04-electron/(a.u.)³ contours. The bonding is nearly isotropic about the Bi site.¹⁹ The planar Bi-O(2) $(sp\sigma)$ bonds extend periodically throughout the crystal along the [100] and [010] directions. However, the corresponding apical-oxygen [O(3)] bond charge is visibly confined, diminishing rapidly in the upper portion of the figure rather than continuing in the direction of the neighboring K⁺ ion (at a distance of ~2.59 Å) in the adjoining layer.

The $BaK_2Bi_2O_7$ density-of-states [N(E)] results in Fig. 4 provide a general overview of the electronic properties for this compound. These results have been calculated using tetrahedral interpolation, based on LAPW results

FIG. 3. Valence-electron charge-density contours on a central (100) plane of $BaK_2Bi_2O_7$. The lower boundary is the basal reflection plane that contains the O(1) atoms. Neighboring layers contain Bi-O(2) and O(3) sites, respectively. The charge densities are expressed in units of electrons/(a.u.)³ and adjacent contours increase by a factor of 2. The 0.02 and 0.04 contours are identified by the short and long dashes, respectively.



FIG. 4. Total and muffin-tin projected density-of-states results for $BaK_2Bi_2O_7$.



at 42 uniformly distributed k points in the $\frac{1}{16}$ irreducible Brillouin-zone wedge. The BaK₂Bi₂O₇ Fermi level falls on the leading edge of a N(E) peak that arises primarily from the weakly bonding p(x,y) states at the O(3) sites that are clustered near E_F in Fig. 2. As discussed in more detail below, Ba \rightarrow K substitution will raise the Fermi level and decrease $N(E_F)$ from the undoped value (~3.7 states/eV cell) to a more typical value (~0.5 states/eV cell) for the $(sp\sigma)^*$ conduction band.

As expected from earlier studies on related tetragonal¹⁴ (Ba₂PbO₄) and nearly-cubic¹⁷ (BaBiO₃ and Ba_{0.5}K_{0.5}BiO₃) phases, the muffin-tin projected Ba and K components are extremely small in the $(sp\sigma)^*$ conduction-band energy range. Thus, these electronically inactive divalent or monovalent constituents are ideal candidates for raising the Fermi level via substitutional doping while minimizing disorder-induced scattering of the conduction electrons near E_F . As Cava *et al.*¹³ have shown, Ba \rightarrow K substitution leads to one interesting possibility, BaK_{2-x}Ba_xBi₂O₇. Clearly, other possible divalent constituents (e.g., BaK_{2-x}Sr_xBi₂O₇, etc.) should also be explored.

As in the cubic $Ba_{1-x}K_xBiO_3$ system,^{1,17} the doping strategy in the alkali-doped bct $Ba_{n+1}Bi_nO_{3n+1}$ homologous series is to lower E_F within the $(sp\sigma)^*$ conduction band(s) in order to stabilize the target bct phase. Though the evidence is limited, there are indications that the tetragonal $Ba_{n+1}Bi_nO_{3n+1}$ compounds may be unstable in the small-*n* limit. For example, efforts to synthesize the undoped n = 1 bct phase, Ba_2BiO_4 , have been unsuccessful thus far.^{6,9,20,21} Instead of the desired tetragonal phase, these studies have shown that, near the 2:1:4 composition range, the Ba-Bi-O system forms an oxygendeficient face-centered-cubic perovskite^{20,21} in which Bi occupies one octahedral site, while a $Bi_{1-x}Ba_x$ mixture occupies the other.

In the case of BaK_{1.3}Ba_{0.7}Bi₂O₇, Cava et al.¹³ have noted that they were unable to synthesize this tetragonal n = 2 Ruddlesden-Popper-type phase through the application of conventional ceramic-processing methods. Instead, it was obtained only through the use of an electrochemical growth technique. X-ray-diffraction evidence indicated that the composition of the electrochemicallydeposited phase could not be changed significantly from the value $x \approx 0.7$ by variations in the preparation conditions. Clearly, these alternative processing methods should also be explored in efforts to produce the alkalidoped n = 1 Ruddlesden-Popper phase, $Ba_{2-x}K_xBiO_4$. One very promising approach involves the use of molecular-beam epitaxy, a technique that has been applied successfully to grow superconducting cubic $Ba_{1-x}Rb_xBiO_3$ and $Ba_{1-x}K_xBiO_3$ thin films.²² This technique may provide a valuable alternative for producing K-doped $Ba_{2-x}K_xBiO_4$ or Ba-enriched $BaK_{2-x}Ba_{x}Bi_{2}O_{7}$ bct-phase samples.

Despite their possibly unstable nature, it is interesting to investigate the electronic structure of the undoped Ba₂BiO₄ and end-member Ba₃Bi₂O₇ compounds. An approximate structure for the 2:1:4 bct phase has been derived from the BaK_{1.3}Ba_{0.7}Bi₂O₇ structural data of Table I. These estimated parameters for Ba₂BiO₄ include the values a = 4.25 Å, c = 13.19 Å, z (Ba)=0.149, and z (O)=0.154. These values are in reasonable agreement with the corresponding Ba₂PbO₄ parameters²³ [a = 4.30Å, c = 13.3 Å, z (Ba)=0.145, and z (O)=0.155]. For the Ba₃Bi₂O₇ calculations, the BaK_{1.3}Ba_{0.7}Bi₂O₇ structural



FIG. 5. LAPW energy-band results for the undoped n = 1 (Ba₂BiO₄) and n = 2 (Ba₃Bi₂O₇) members of the Ba_{n+1}Bi_nO_{3n+1} homologous series. Bands with specific orbital character are labeled in accordance with Fig. 2.

parameters of Table I have been used directly.

The results of LAPW calculations for these bct forms of Ba₂BiO₄ and Ba₃Bi₂O₇ are shown in Fig. 5. In these materials, the Fermi level is raised so that the $(sp\sigma)^*$ band(s) is half filled. Overall, the Ba₂BiO₄ bands are extremely similar to the earlier Ba₂PbO₄ results, ¹⁴ although the increased Bi(6s) binding energy has reduced the calculated 1.7 eV semiconductor gap in Ba₂PbO₄ to a 1.1-eV gap separating the lowest $(sp\sigma)^*$ state at Γ and the top of the nonbonding O(2p) manifold at X. The lower portions of the Ba(5d) bands lie slightly above E_F and intersect the $(sp\sigma)^*$ band near X, in a manner similar to the Ba₂PbO₄ results.

Below E_F , the Ba₃Bi₂O₇ results in Fig. 5 are in good qualitative agreement with the corresponding BaK₂Bi₂O₇ bands of Fig. 2. The main changes occur above E_F , where the Ba(5d) bands have dropped in energy to the point where they nearly intersect the Fermi level. This could be a partial consequence of neglecting alloyinginduced changes in the assumed structure for the BaK_{2-x}Ba_xBi₂O₇ system. Nevertheless, the close similarities between the BaK₂Bi₂O₇ (Fig. 2) and Ba₃Bi₂O₇ (Fig. 5) conduction-band results provides strong justification for the rigid-band treatment of the intermediate BaK_{2-x}Ba_xBi₂O₇ alloys.

An expanded plot of the $(sp\sigma)^*$ conduction bands and the corresponding density of states for this system, as derived from the BaK₂Bi₂O₇ results, is shown in Fig. 6. The interior scale presents the rigid-band variation of $E_F(x)$ with doping in the BaK_{2-x}Ba_xBi₂O₇ alloys. As indicated, N(E,x) decreases rapidly for x > 0 and then increases quite gradually to the value 0.53 states/eV cell (or 0.27 states/eV Bi) for x = 0.7, the composition of the nonsuperconducting electrochemically-prepared material.¹³ For purposes of comparison, the corresponding rigid-band density-of-states values¹⁷ for the cubic $Ba_{1-r}K_rBiO_3$, compounds near the maximum- T_c composition $x \approx 0.3 - 0.4$ are in the range 0.46 - 0.52 states/eV Bi. Thus, the failure to observe superconductivity in $BaK_{1,3}Ba_{0,7}Bi_{2}O_{7}$ may be due in part to the reduced value of $N(E_F)$ for the bct versus the cubic phase.

As discussed previously,¹⁴ there are also geometrical factors that favor an enhanced electron-phonon coupling in the cubic phase relative to its tetragonal counterparts. Namely, an analysis based on a simple tight-binding model¹⁶ shows that the electron-phonon-coupling strength of the cubic $(sp\sigma)^*$ band is focused strongly near half filling and is enhanced by the fact that there are a larger number (i.e., 6 vs 4) of face-shared oxygen neighbors. The corresponding coupling in the bct compounds is more diffuse; while the face-sharing oxygen contributions remain at half filling, the corresponding apical-oxygen interactions are concentrated near the $(sp\sigma)^*$ conduction-

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BaK_{2-x}Ba_xBi₂O₇

FIG. 6. Calculated variation of the $BaK_{2-x}Ba_xBi_2O_7$ Fermi level $E_F(x)$ with x within the $(sp\sigma)^*$ conduction bands according to a rigid-band treatment.

band edges.

According to the results in Fig. 6, this suggests that $BaK_{2-x}Ba_xBi_2O_7$ alloys with an increased Ba content $x \ge 1$ should provide more favorable band properties for possible superconductivity. Not only is the density of states increased significantly (~0.7-0.8 states /eV Bi), but the electron-phonon-coupling strength should also be enhanced by the added contribution from the apical oxygens.

To summarize, the electronic band properties of the n = 1 and n = 2 members of the bct Ruddlesden-Popper homologous series have been calculated and analyzed, with particular emphasis on the n = 2 alloy, BaK_{2-x}Ba_xBi₂O₇. A rigid-band treatment of this phase, based on LAPW results for the end-member compounds BaK₂Bi₂O₇ and Ba₃Bi₂O₇, suggests that an increased Ba concentration $(x \ge 1)$ should provide band properties near E_F that are more favorable for superconductivity than the $x \approx 0.7$ (BaK_{1.3}Ba_{0.7}Bi₂O₇) composition that has been prepared electrochemically and found not to superconduct. The results also suggest that the single-layer K-doped Ba_{2-x}K_xBiO₄ bct phase is an equally promising high- T_c candidate.

ACKNOWLEDGMENTS

I am pleased to thank my colleagues R. J. Cava, E. H. Hartford, E. S. Hellman, and T. Siegrist for several valuable discussions on the subject of this investigation.

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FIG. 1. Primitive body-centered-tetragonal unit cell for $BaK_{2-x}Ba_xBi_2O_7$. Oxygens in the Ba, Bi, and K-Ba planes are denoted O(1), O(2), and O(3), respectively.